

NTD4805N, NVD4805N

MOSFET – Power, Single, N-Channel, DPAK/IPAK 30 V, 88 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current ($R_{\theta JA}$) (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	17.4	A
		$T_A = 85^{\circ}\text{C}$		13.5	
$T_A = 25^{\circ}\text{C}$		P_D	2.65	W	
Continuous Drain Current ($R_{\theta JA}$) (Note 2)		$T_A = 25^{\circ}\text{C}$	I_D	12.7	A
		$T_A = 85^{\circ}\text{C}$		9.8	
Power Dissipation ($R_{\theta JA}$) (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	1.41	W
Continuous Drain Current ($R_{\theta JC}$) (Note 1)		$T_C = 25^{\circ}\text{C}$	I_D	95	A
		$T_C = 85^{\circ}\text{C}$		73	
Power Dissipation ($R_{\theta JC}$) (Note 1)		$T_C = 25^{\circ}\text{C}$	P_D	79	W
Pulsed Drain Current	$t_p=10\mu\text{s}$	$T_A = 25^{\circ}\text{C}$	I_{DM}	175	A
Current Limited by Package		$T_A = 25^{\circ}\text{C}$	$I_{DmaxPkg}$	45	A
Operating Junction and Storage Temperature			T_J, T_{stg}	-55 to 175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	55	A
Source Current (Body Diode) Pulsed $t_p=20\mu\text{s}$			I_{SM}	175	A
Drain to Source dV/dt			dV/dt	6.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 24\text{ V}$, $V_{GS} = 10\text{ V}$, $L = 1.0\text{ mH}$, $I_{L(pk)} = 24\text{ A}$, $R_G = 25\ \Omega$)			E_{AS}	288	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

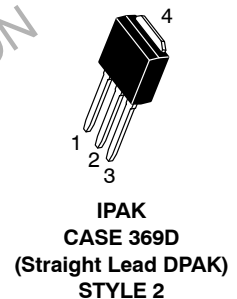
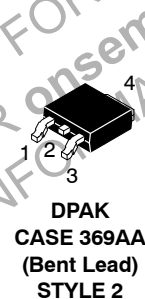
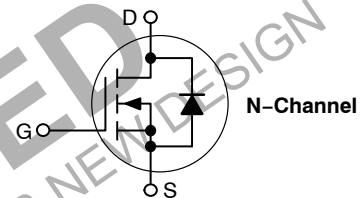
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



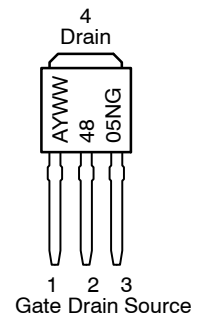
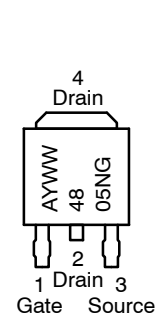
ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	5.0 m Ω @ 10 V	88 A
	7.4 m Ω @ 4.5 V	



MARKING DIAGRAMS & PIN ASSIGNMENTS



A = Assembly Location*
Y = Year
WW = Work Week
4805N = Device Code
G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.9	°C/W
Junction-to-TAB (Drain)	$R_{\theta JC-TAB}$	3.5	
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	56.6	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	106.6	

1. Surface-mounted on FR4 board using 1 in sq pad size, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			27		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.5		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.86		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ to }11.5\text{ V}$	$I_D = 30\text{ A}$	4.3	5.0	m Ω
			$I_D = 15\text{ A}$	4.2		
		$V_{GS} = 4.5\text{ V}$	$I_D = 30\text{ A}$	6.0	7.4	
			$I_D = 15\text{ A}$	5.8		
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		17		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 12\text{ V}$		2865		pF
Output Capacitance	C_{oss}			610		
Reverse Transfer Capacitance	C_{rss}			338		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		20.5	26	nC
Threshold Gate Charge	$Q_{G(TH)}$			4.05		
Gate-to-Source Charge	Q_{GS}			8.28		
Gate-to-Drain Charge	Q_{GD}			8.36		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		48		nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		17.2		ns
Rise Time	t_r			20.3		
Turn-Off Delay Time	$t_{d(off)}$			20.8		
Fall Time	t_f			8.0		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		10.8		ns
Rise Time	t_r			20.5		
Turn-Off Delay Time	$t_{d(off)}$			30.8		
Fall Time	t_f			4.4		

NTD4805N, NVD4805N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}$, $I_S = 30\text{ A}$	$T_J = 25^\circ\text{C}$		0.87	1.2	V
			$T_J = 125^\circ\text{C}$		0.76		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}$, $dI_S/dt = 100\text{ A}/\mu\text{s}$, $I_S = 30\text{ A}$			25.7		ns
Charge Time	t_a				13.1		
Discharge Time	t_b				12.6		
Reverse Recovery Time	Q_{RR}				18		nC

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		2.49		nH
Drain Inductance, DPAK	L_D			0.0164		
Drain Inductance, IPAK	L_D			1.88		
Gate Inductance	L_G			3.46		
Gate Resistance	R_G			0.8		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

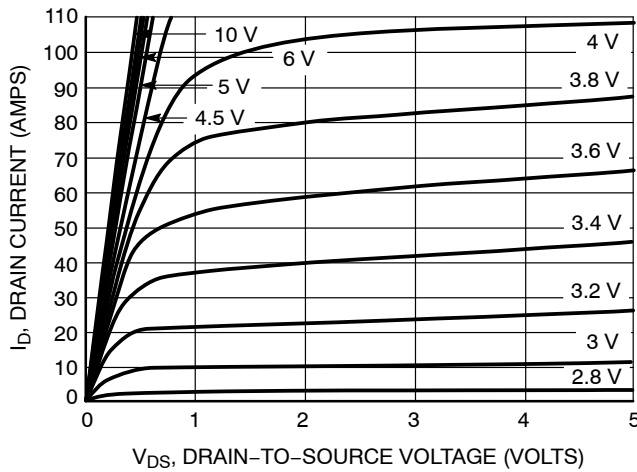


Figure 1. On-Region Characteristics

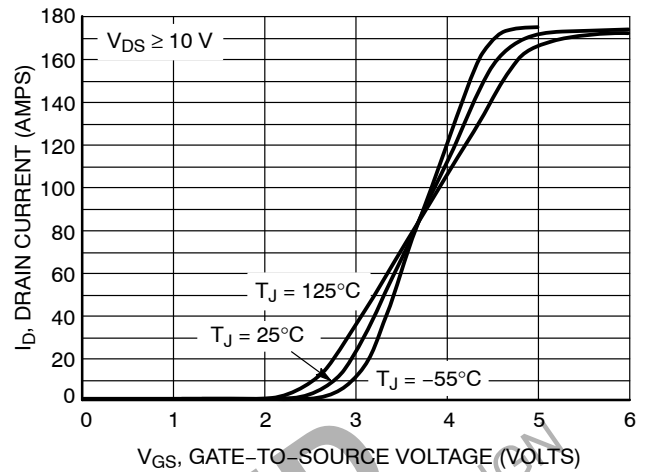


Figure 2. Transfer Characteristics

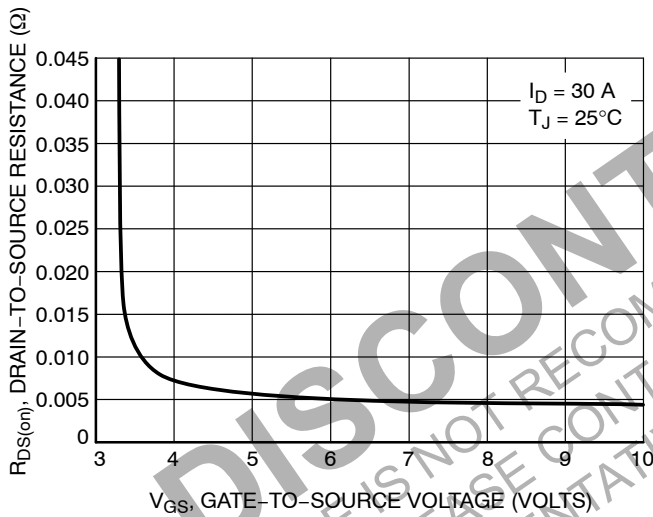


Figure 3. On-Resistance vs. Gate-to-Source Voltage

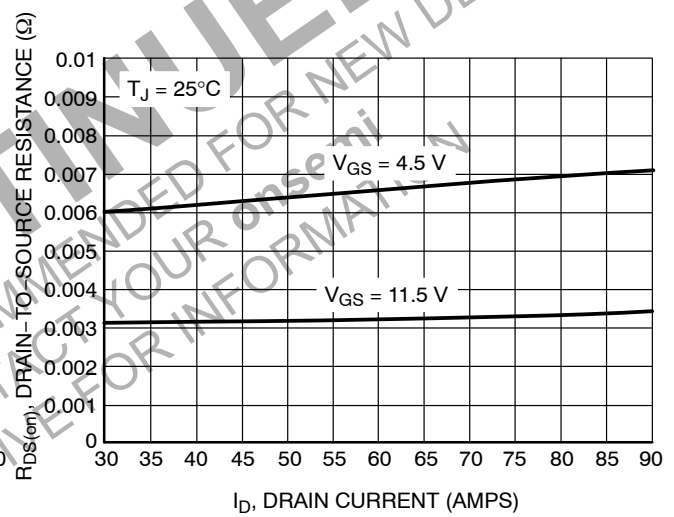


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

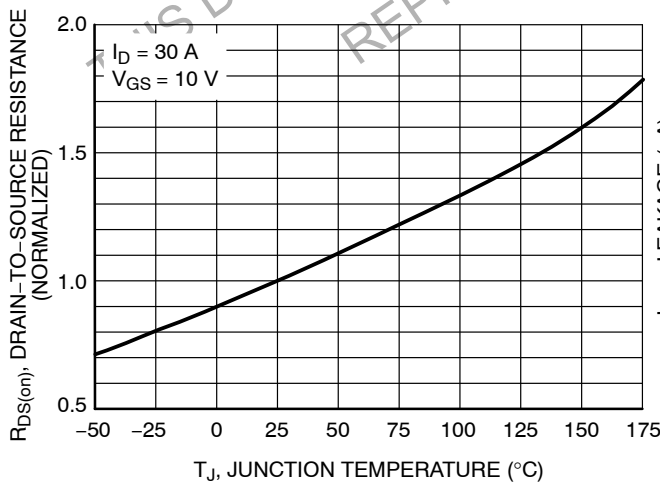


Figure 5. On-Resistance Variation with Temperature

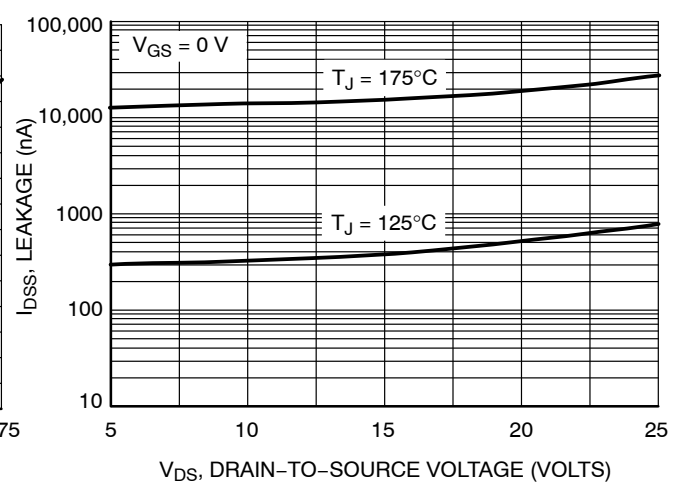


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

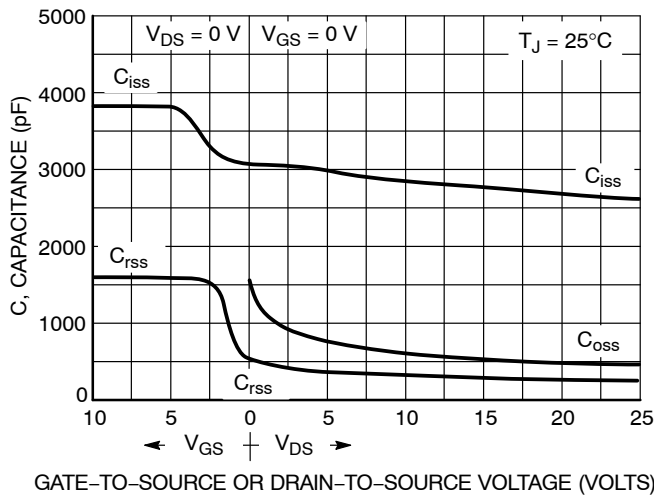


Figure 7. Capacitance Variation

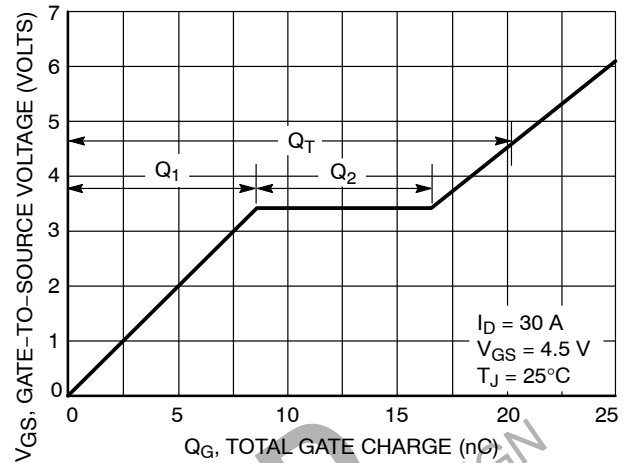


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

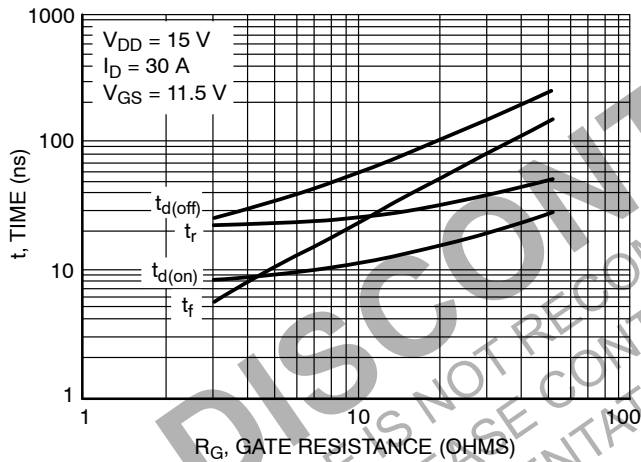


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

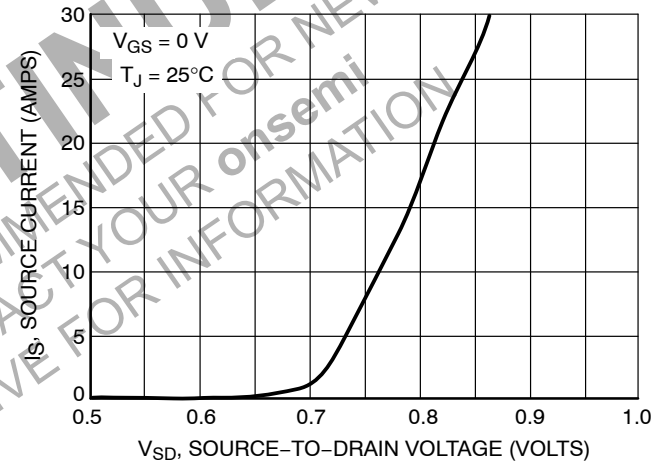


Figure 10. Diode Forward Voltage vs. Current

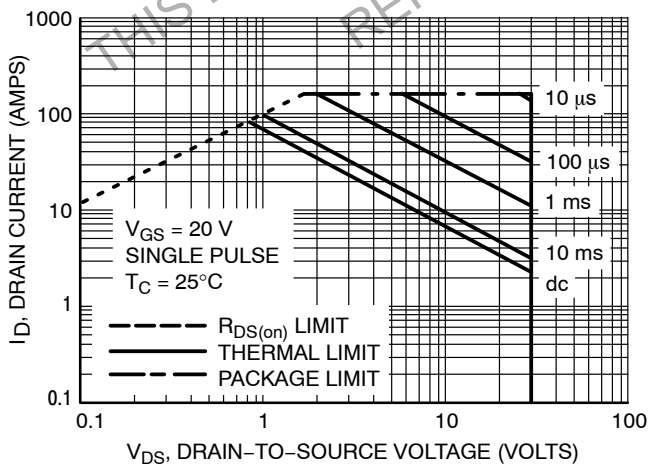


Figure 11. Maximum Rated Forward Biased Safe Operating Area

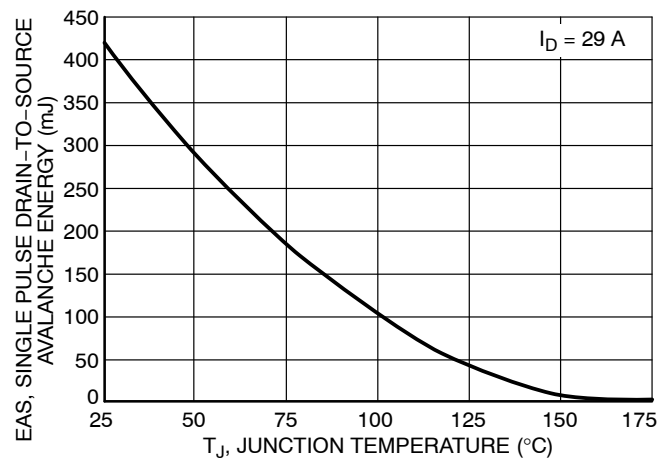


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL PERFORMANCE CURVES

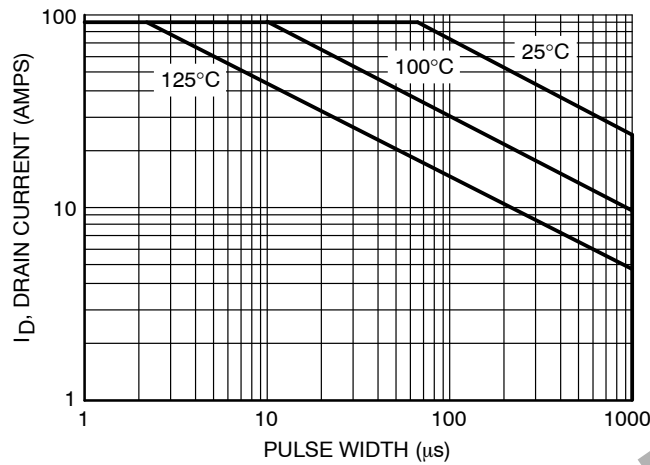


Figure 13. Avalanche Characteristics

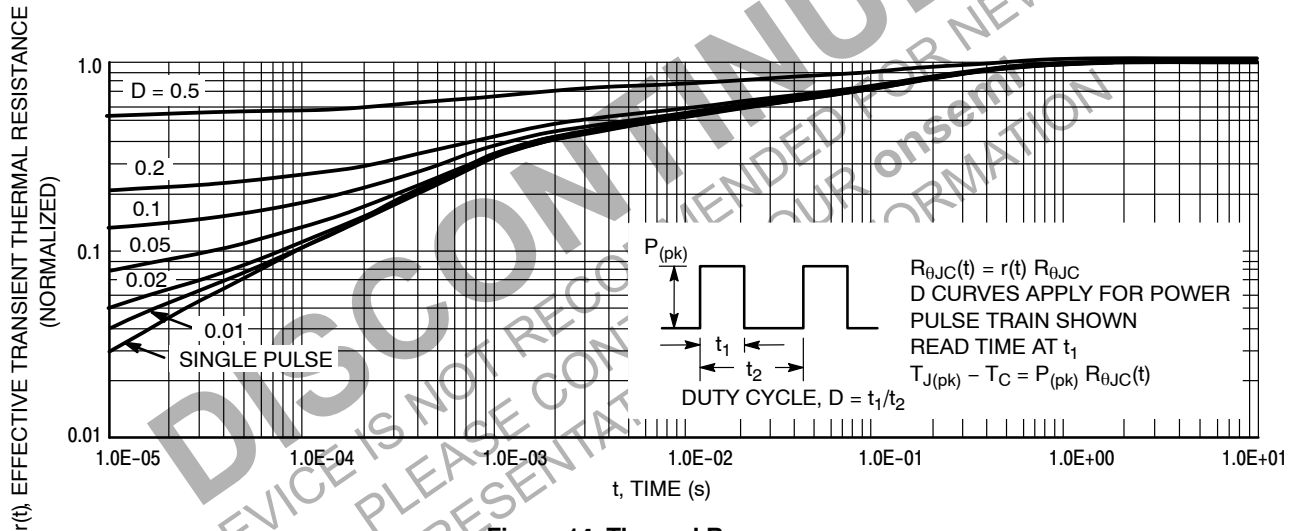


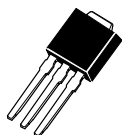
Figure 14. Thermal Response

ORDERING INFORMATION

Order Number	Package	Shipping [†]
NTD4805NT4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NTD4805N-1G	IPAK (Pb-Free)	75 Units / Rail
NVD4805NT4G*	DPAK (Pb-Free)	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

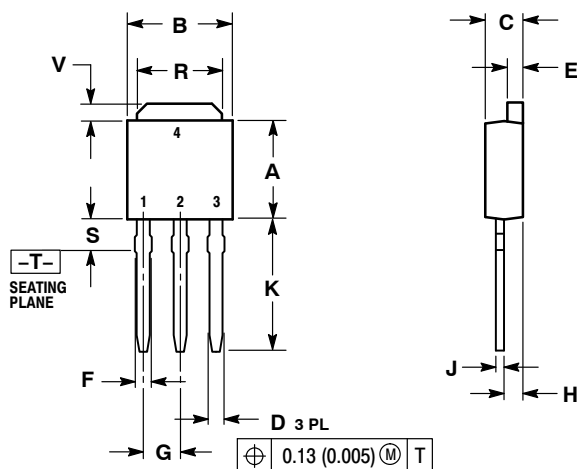
*NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



DPAK INSERTION MOUNT
CASE 369
ISSUE O

DATE 02 JAN 2000

SCALE 1:1



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

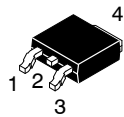
STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

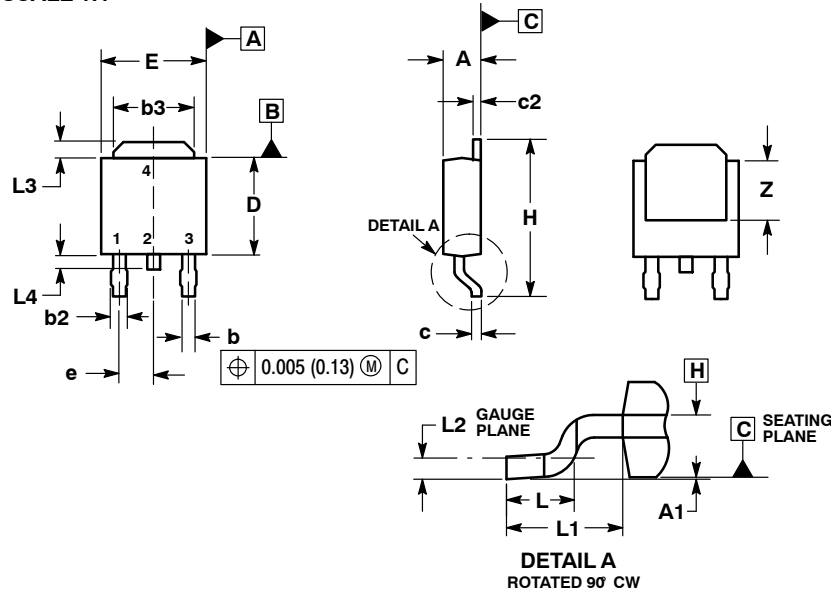
STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

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SCALE 1:1



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

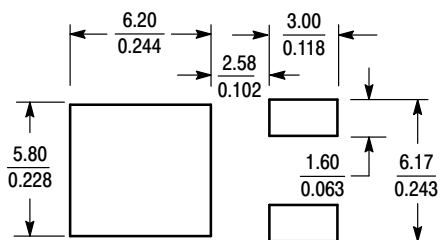
STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



SCALE 3:1 (mm/inches)

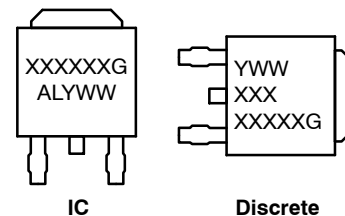
*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

GENERIC
MARKING DIAGRAM*



XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

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